
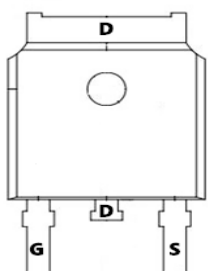




TMN10030D

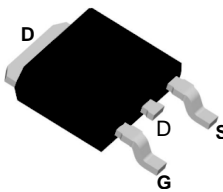
N-Channel Enhancement Mosfet

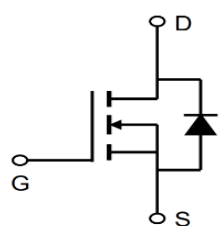
<p>General Description</p> <ul style="list-style-type: none"> • Low $R_{DS(ON)}$ • RoHS and Halogen-Free Compliant <p>Applications</p> <ul style="list-style-type: none"> • Load switch • PWM 	<p>General Features</p> <p>$V_{DS} = 100V$ $I_D = 30A$</p> <p>$R_{DS(ON)} = 32m\Omega (typ.) @ V_{GS} = 10V$</p> <p>100% UIS Tested 100% R_g Tested</p> 
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Marking 30N10

D:TO-252-3L





Absolute Maximum Ratings ($T_C = 25^\circ C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	30	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	15	A
I_{DM}	Pulsed Drain Current ²	80	A
EAS	Single Pulse Avalanche Energy ³	4.0	mJ
I_{AS}	Avalanche Current	30	A
$P_D @ T_C = 25^\circ C$	Total Power Dissipation ³	43.7	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹	---	50	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	3.0	$^\circ C/W$



TMN10030D

N-Channel Enhancement Mosfet

Electrical Characteristics (T_J = 25°C, unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit	
Static Characteristics							
Drain-Source Breakdown Voltage	V_{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	100	-	-	V	
Gate-body Leakage current	I_{GSS}	V _{DS} = 0V, V _{GS} = ±20V	-	-	±100	nA	
Zero Gate Voltage Drain Current	I_{DSS}	V _{DS} = 100V, V _{GS} = 0V	T _J = 25°C	-	-	1	μA
			T _J = 100°C	-	-	100	
Gate-Threshold Voltage	V_{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	1.2	-	2.5	V	
Drain-Source on-Resistance ⁴	R_{DS(on)}	V _{GS} = 10V, I _D = 5A	-	32	45	mΩ	
		V _{GS} = 4.5V, I _D = 3A	-	38	75		
Forward Transconductance ⁴	g_{fs}	V _{DS} = 5V, I _D = 5A	-	12	-	S	
Dynamic Characteristics⁵							
Input Capacitance	C_{iss}	V _{DS} = 15V, V _{GS} = 0V, f = 1MHz	-	2420	-	pF	
Output Capacitance	C_{oss}		-	99	-		
Reverse Transfer Capacitance	C_{rss}		-	84	-		
Gate Resistance	R_g	f = 1MHz	-	1.3	-	Ω	
Switching Characteristics⁵							
Total Gate Charge	Q_g	V _{GS} = 10V, V _{DS} = 50V, I _D = 5A	-	40.6	-	nC	
Gate-Source Charge	Q_{gs}		-	8	-		
Gate-Drain Charge	Q_{gd}		-	6.7	-		
Turn-On Delay Time	t_{d(on)}	V _{GS} = 10V, V _{DD} = 50V, R _G = 3Ω, I _D = 5A	-	8.7	-	ns	
Rise Time	t_r		-	41	-		
Turn-Off Delay Time	t_{d(off)}		-	40	-		
Fall Time	t_f		-	32	-		
Drain-Source Body Diode Characteristics							
Diode Forward Voltage ⁴	V_{SD}	I _S = 1A, V _{GS} = 0V	-	-	1.2	V	
Continuous Source Current	I_S	T _C = 25°C	-	-	30	A	

Notes:

1. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)} = 150°C.
2. The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
3. The EAS data shows Max. rating. The test condition is V_{DD} = 25V, V_{GS} = 10V, L = 0.1mH, I_{AS} = 8A
4. The power dissipation is limited by 150°C junction temperature
5. The data is theoretically the same as I_D and I_{DM}, in real applications, should be limited by total power dissipation.



TMN10030D

N-Channel Enhancement Mosfet

Typical Characteristics

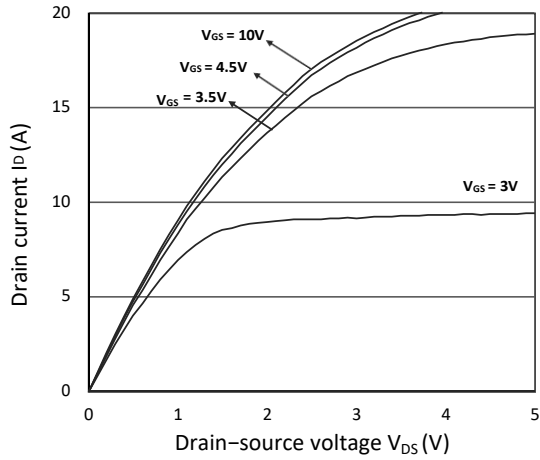


Figure 1. Output Characteristics

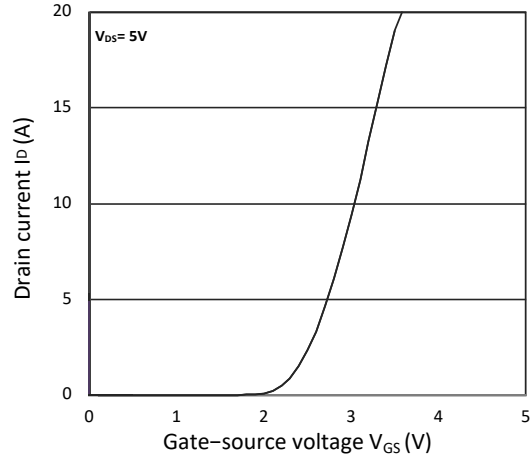


Figure 2. Transfer Characteristics

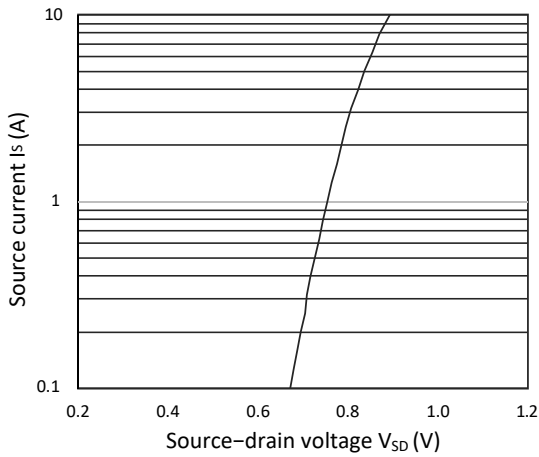


Figure 3. Forward Characteristics of Reverse

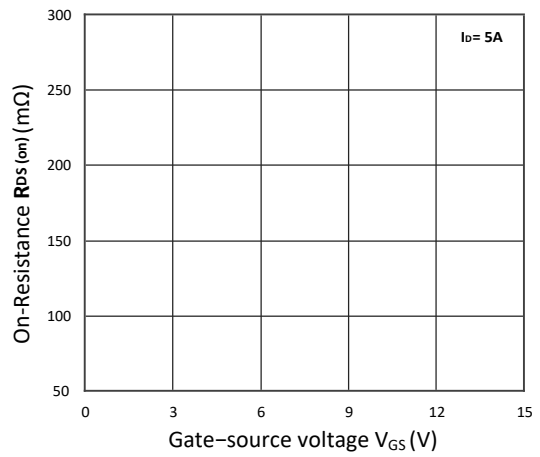


Figure 4. $R_{DS(on)}$ vs. V_{GS}

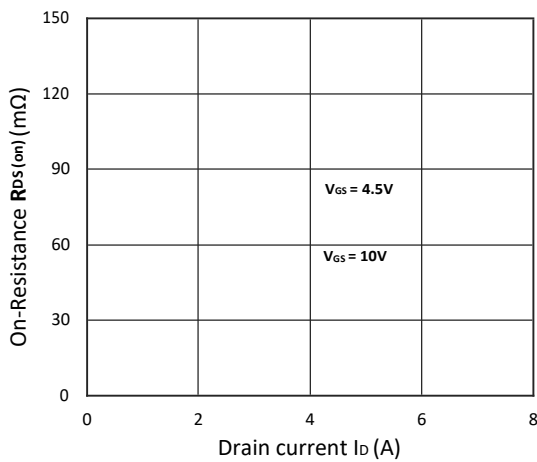


Figure 5. $R_{DS(on)}$ vs. I_D

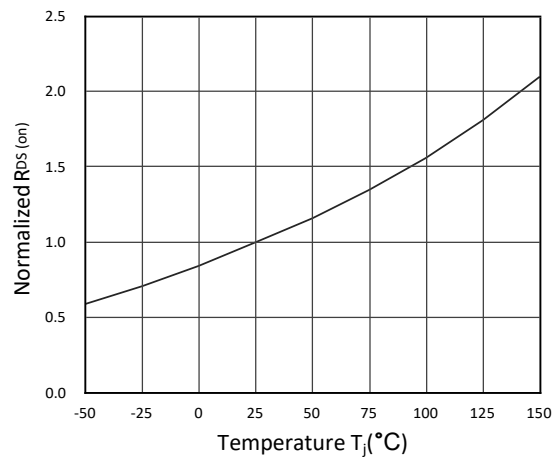


Figure 6. Normalized $R_{DS(on)}$ vs. Temperature

TMN10030D

N-Channel Enhancement Mosfet

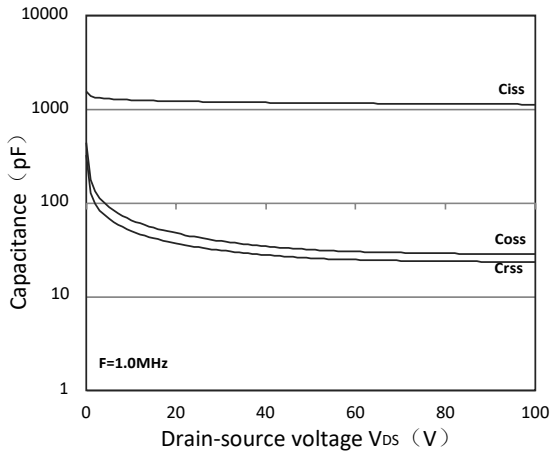


Figure 7. Capacitance Characteristics

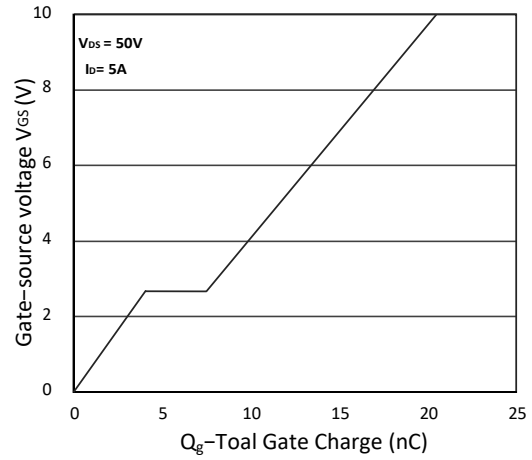


Figure 8. Gate Charge Characteristics

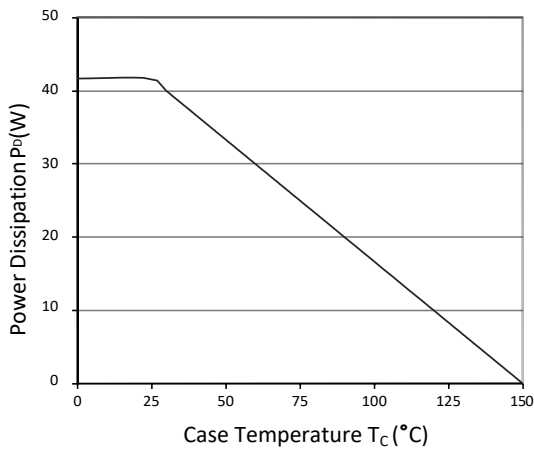


Figure 9. Power Dissipation

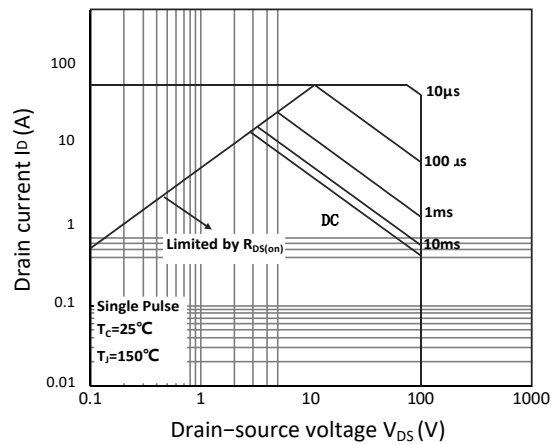


Figure 10. Safe Operating Area

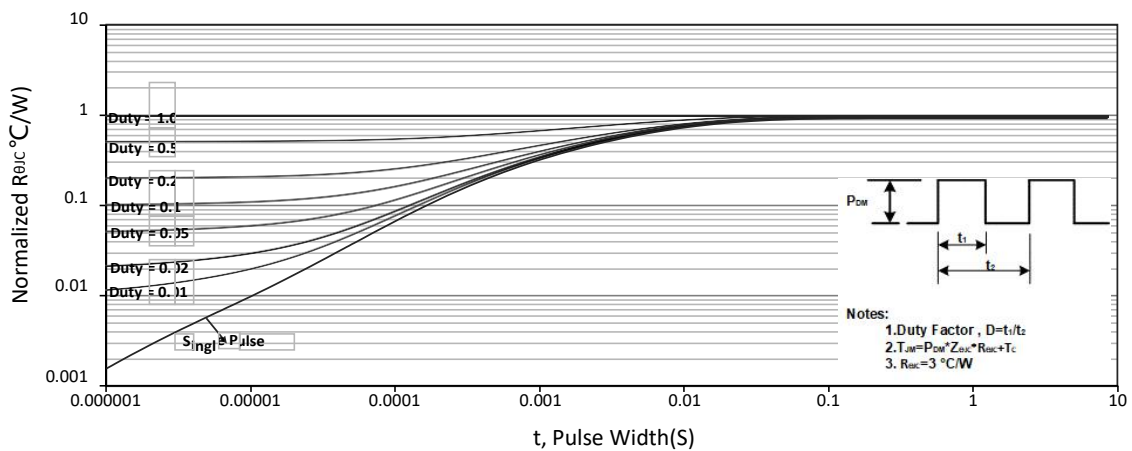
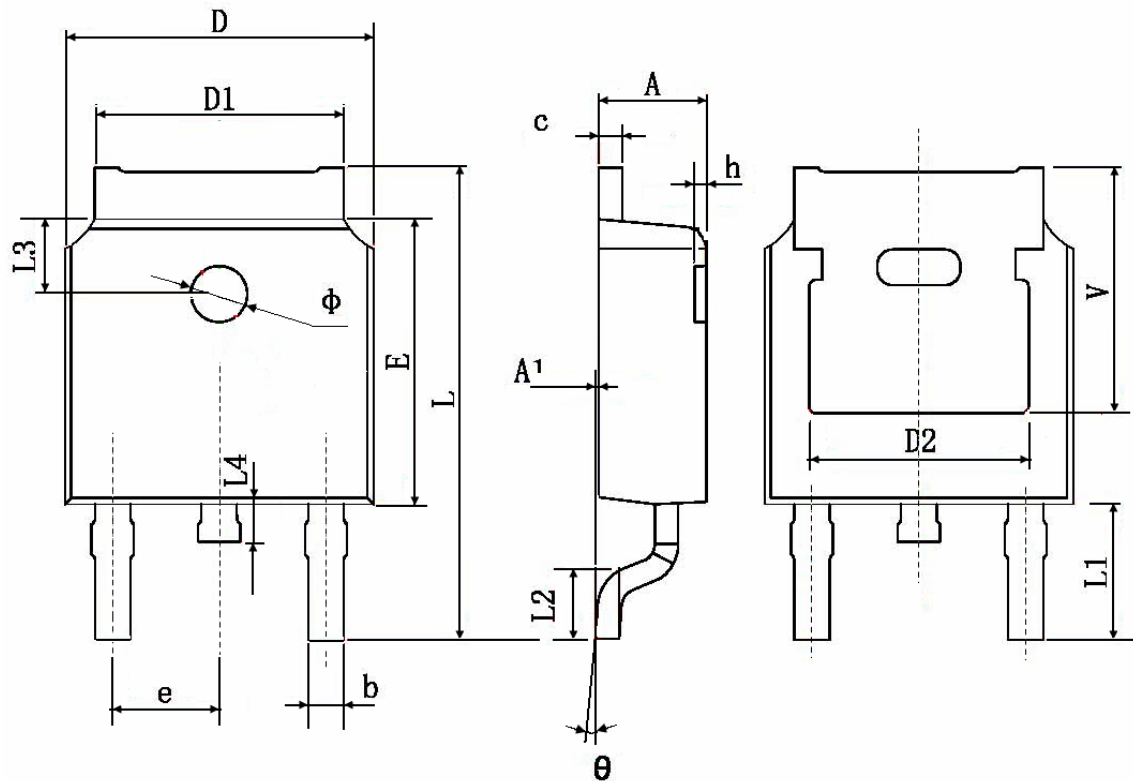


Figure 11. Normalized Maximum Transient Thermal Impedance

Package Mechanical Data: TO-252-3L



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	